

LF155/LF156/LF256/LF257/LF355/LF356/LF357 JFET Input Operational Amplifiers

General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET™ Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Features

Advantages

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance—very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

Applications

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers

■ Logarithmic amplifiers

- Photocell amplifiers
- Sample and Hold circuits

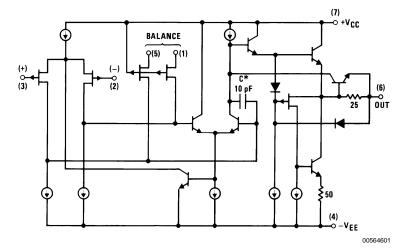
Common Features

- Low input bias current: 30pA
- Low Input Offset Current: 3pA
- High input impedance: $10^{12}\Omega$
- Low input noise current: $0.01 \text{ pA}/\sqrt{\text{Hz}}$
- High common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

Uncommon Features

		LF155/ LF355	LF156/ LF256/ LF356	LF257/ LF357 (A _V =5)	Units
	Extremely fast settling time to 0.01%	4	1.5	1.5	μs
•	Fast slew rate	5	12	50	V/µs
	Wide gain bandwidth	2.5	5	20	MHz
•	Low input noise voltage	20	12	12	nV/√Hz

Simplified Schematic



*3pF in LF357 series.

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Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

	LF155/6	LF256/7/LF356B	LF355/6/7
Supply Voltage	±22V	±22V	±18V
Differential Input Voltage	±40V	±40V	±30V
Input Voltage Range (Note 2)	±20V	±20V	±16V
Output Short Circuit Duration	Continuous	Continuous	Continuous
T _{JMAX}			
H-Package	150°C	115°C	115°C
N-Package		100°C	100°C
M-Package		100°C	100°C
Power Dissipation at $T_A = 25^{\circ}C$ (Notes			
1, 8)			
H-Package (Still Air)	560 mW	400 mW	400 mW
H-Package (400 LF/Min Air Flow)	1200 mW	1000 mW	1000 mW
N-Package		670 mW	670 mW
M-Package		380 mW	380 mW
Thermal Resistance (Typical) θ_{JA}			
H-Package (Still Air)	160°C/W	160°C/W	160°C/W
H-Package (400 LF/Min Air Flow)	65°C/W	65°C/W	65°C/W
N-Package		130°C/W	130°C/W
M-Package		195°C/W	195°C/W
(Typical) θ_{JC}			
H-Package	23°C/W	23°C/W	23°C/W
Storage Temperature Range	-65°C to +150°C	-65°C to +150°C	-65°C to +150°C
Soldering Information (Lead Temp.)			
Metal Can Package			
Soldering (10 sec.)	300°C	300°C	300°C
Dual-In-Line Package			
Soldering (10 sec.)	260°C	260°C	260°C
Small Outline Package			
Vapor Phase (60 sec.)		215°C	215°C
Infrared (15 sec.)		220°C	220°C
See AN-450 "Surface Mounting Methods	and Their Effect on P	roduct Reliability" for	other methods of
soldering surface mount devices.			
ESD tolerance			

ESD tolerance

(100 pF discharged through $1.5k\Omega$) 1000V 1000V 1000V

DC Electrical Characteristics

(Note 3)

Symbol	Parameter	Conditions	LF155/6			LF256/7 LF356B			ι	Units		
			Min	Тур	Max	Min Typ Max			Min	Тур	Max	
Vos	Input Offset Voltage	$R_S=50\Omega$, $T_A=25^{\circ}C$		3	5		3	5		3	10	mV
		Over Temperature			7			6.5			13	mV
$\Delta V_{OS}/\Delta T$	Average TC of Input Offset Voltage	$R_S=50\Omega$		5			5			5		μV/°C
ΔTC/ΔV _{OS}	Change in Average TC with V _{OS} Adjust	$R_S=50\Omega$, (Note 4)		0.5			0.5			0.5		μV/°C per mV
I _{os}	Input Offset Current	T _J =25°C, (Notes 3, 5)		3	20		3	20		3	50	рА
		T _J ≤T _{HIGH}			20			1			2	nA

DC Electrical Characteristics (Continued)

(Note 3)

Symbol	Parameter	Conditions	LF155/6			LF256/7 LF356B			ı	Units		
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
I _B	Input Bias Current	T _J =25°C, (Notes 3, 5)		30	100		30	100		30	200	pА
		T _J ≤T _{HIGH}			50			5			8	nA
R _{IN}	Input Resistance	T _J =25°C		10 ¹²			10 ¹²			10 ¹²		Ω
A _{VOL}	Large Signal Voltage	V _S =±15V, T _A =25°C	50	200		50	200		25	200		V/mV
	Gain	$V_O = \pm 10V$, $R_L = 2k$										
		Over Temperature	25			25			15			V/mV
Vo	Output Voltage Swing	V _S =±15V, R _L =10k	±12	±13		±12	±13		±12	±13		V
		$V_S=\pm 15V$, $R_L=2k$	±10	±12		±10	±12		±10	±12		V
V _{CM}	Input Common-Mode	V _S =±15V	±11	+15.1		±11	±15.1		+10	+15.1		V
	Voltage Range		_ <u> </u>	-12		T 1 1	-12	+10		-12		V
CMRR	Common-Mode		85	100		85	100		80	100		dB
	Rejection Ratio		00	100		65	100		80	100		uБ
PSRR	Supply Voltage	(Note 6)	85	100		85	100		80	100		dB
	Rejection Ratio		0.5	100		00	100		00	100		L

DC Electrical Characteristics

 $T_A = T_J = 25^{\circ}C, V_S = \pm 15V$

Parameter	LF ²	155	LF:	355	LF156/256	256/257/356B LF356 LF357			357	Units	
	Тур	Max	Тур	Max	Тур	Max	Тур	Max	Тур Мах	Ullits	
Supply Current	2	4	2	4	5	7	5	10	5	10	mA

AC Electrical Characteristics

 $T_A = T_J = 25^{\circ}C, V_S = \pm 15V$

	_	0 1141	LF155/355	LF156/256/	LF156/256/356/	LF257/357	
Symbol	Parameter	Conditions		356B	LF356B		Units
			Тур	Min	Тур	Тур	
SR	Slew Rate	LF155/6:	5	7.5	12		V/µs
		A _V =1,					
		LF357: A _V =5				50	V/µs
GBW	Gain Bandwidth Product		2.5		5	20	MHz
t _s	Settling Time to 0.01%	(Note 7)	4		1.5	1.5	μs
e _n	Equivalent Input Noise	R _S =100Ω					
	Voltage	f=100 Hz	25		15	15	nV/√Hz
		f=1000 Hz	20		12	12	nV/√Hz
i _n	Equivalent Input Current	f=100 Hz	0.01		0.01	0.01	pA/√Hz
	Noise	f=1000 Hz	0.01		0.01	0.01	pA/√Hz
C _{IN}	Input Capacitance		3		3	3	pF

Notes for Electrical Characteristics

Note 1: The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by T_{JMAX} , θ_{JA} , and the ambient temperature, T_A . The maximum available power dissipation at any temperature is $P_D = (T_{JMAX} - T_A)/\theta_{JA}$ or the 25°C P_{dMAX} , whichever is less.

Note 2: Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.

Note 3: Unless otherwise stated, these test conditions apply:

Notes for Electrical Characteristics (Continued)

	LF155/156	LF256/257	LF356B	LF355/6/7
Supply Voltage, V _S	±15V ≤ V _S ≤ ±20V	±15V ≤ V _S ≤ ±20V	±15V ≤ V _S ±20V	V _S = ±15V
T_A	$-55^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	$-25^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$	$0^{\circ}\text{C} \leq \text{T}_{\text{A}} \leq +70^{\circ}\text{C}$	$0^{\circ}\text{C} \leq \text{T}_{\text{A}} \leq +70^{\circ}\text{C}$
T _{HIGH}	+125°C	+85°C	+70°C	+70°C

and V_{OS} , I_B and I_{OS} are measured at V_{CM} = 0.

Note 4: The Temperature Coefficient of the adjusted input offset voltage changes only a small amount (0.5µV/°C typically) for each mV of adjustment from its original unadjusted value. Common-mode rejection and open loop voltage gain are also unaffected by offset adjustment.

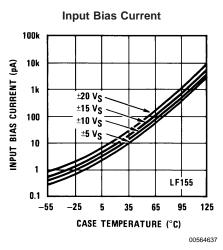
Note 5: The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature, T_J . Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, Pd. $T_J = T_A + \theta_{JA}$ Pd where θ_{JA} is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

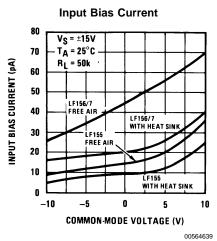
Note 6: Supply Voltage Rejection is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

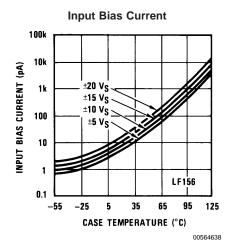
Note 7: Settling time is defined here, for a unity gain inverter connection using $2 k\Omega$ resistors for the LF155/6. It is the time required for the error voltage (the voltage at the inverting input pin on the amplifier) to settle to within 0.01% of its final value from the time a 10V step input is applied to the inverter. For the LF357, $A_V = -5$, the feedback resistor from output to input is $2k\Omega$ and the output step is 10V (See Settling Time Test Circuit).

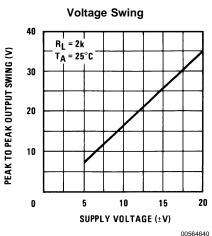
Note 8: Max. Power Dissipation is defined by the package characteristics. Operating the part near the Max. Power Dissipation may cause the part to operate outside guaranteed limits.

Typical DC Performance Characteristics Curves are for LF155 and LF156 unless otherwise specified.

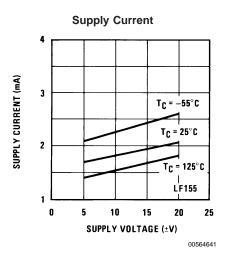


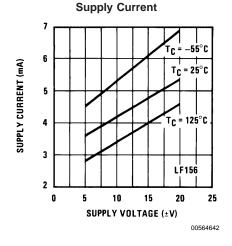


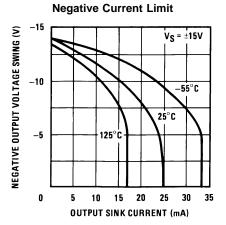


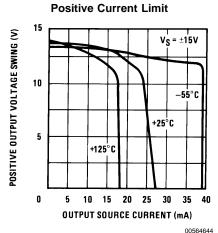


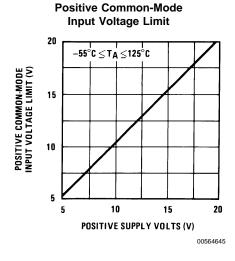
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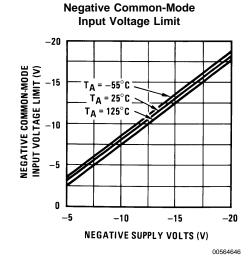




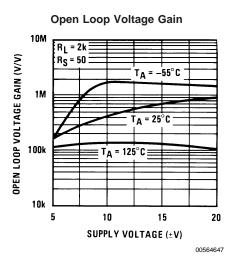


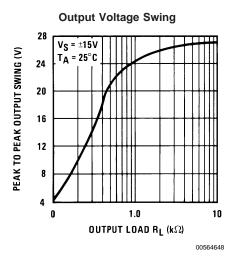




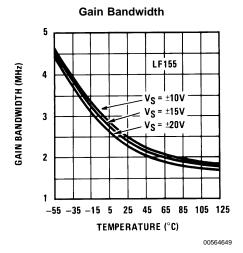


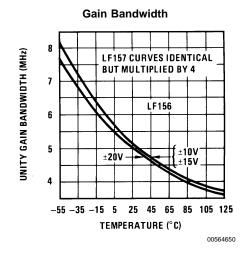
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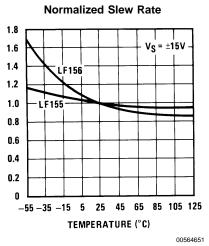


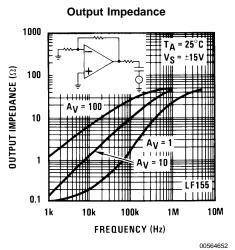


Typical AC Performance Characteristics



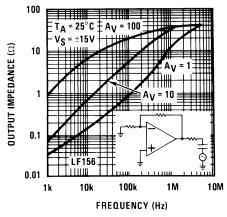




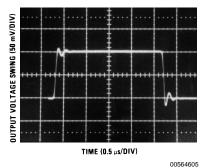


Typical AC Performance Characteristics (Continued)



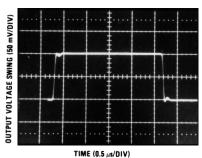


LF155 Small Signal Pulse Response, $A_V = +1$



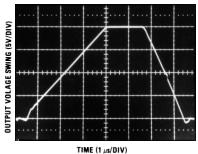
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LF156 Small Signal Pulse Response, $A_V = +1$



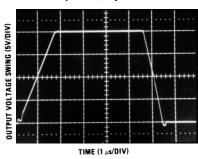
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LF155 Large Signal Pulse Response, $A_V = +1$



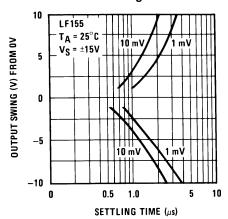
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LF156 Large Signal Puls Response, A_V = +1



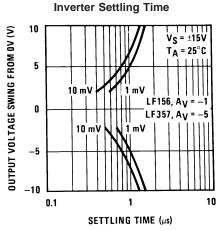
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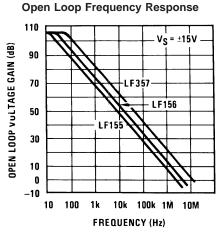
Inverter Settling Time

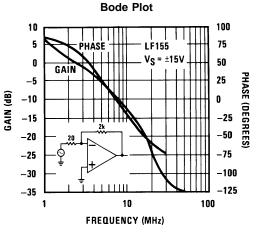


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Typical AC Performance Characteristics (Continued)







Bode Plot

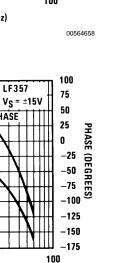
FREQUENCY (MHz)

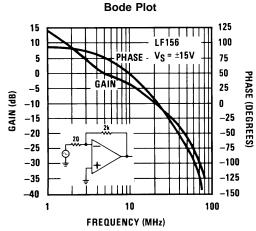
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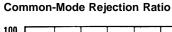
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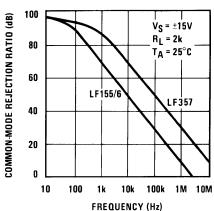
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-20



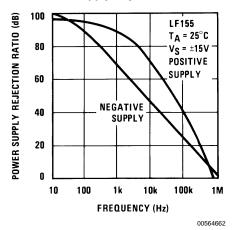




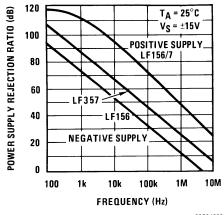


Typical AC Performance Characteristics (Continued)

Power Supply Rejection Ratio

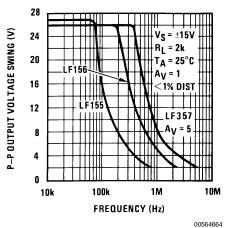


Power Supply Rejection Ratio

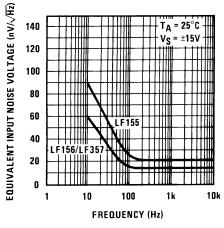


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Undistorted Output Voltage Swing

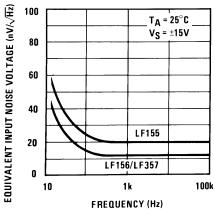


Equivalent Input Noise Voltage



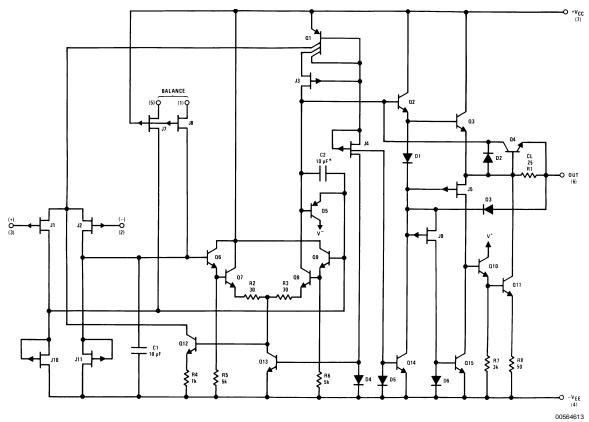
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Equivalent Input Noise Voltage (Expanded Scale)



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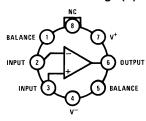
Detailed Schematic



*C = 3pF in LF357 series.

Connection Diagrams (Top Views)

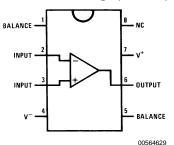
Metal Can Package (H)



Order Number LF155H, LF156H, LF256H, LF257H, LF356BH, LF356H, or LF357H See NS Package Number H08C

*Available per JM38510/11401 or JM38510/11402

Dual-In-Line Package (M and N)



Order Number LF356M, LF356MX, LF355N, or LF356N See NS Package Number M08A or N08E

Application Hints

These are op amps with JFET input devices. These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore large differential input voltages can easily be accommodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will force the output to a high state, potentially causing a

Application Hints (Continued)

reversal of phase to the output. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output however, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

These amplifiers will operate with the common-mode input voltage equal to the positive supply. In fact, the common-mode voltage can exceed the positive supply by approximately 100 mV independent of supply voltage and over the full operating temperature range. The positive supply can therefore be used as a reference on an input as, for example, in a supply current monitor and/or limiter.

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

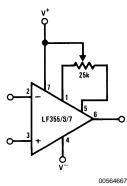
All of the bias currents in these amplifiers are set by FET current sources. The drain currents for the amplifiers are therefore essentially independent of supply voltage.

As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pickup" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

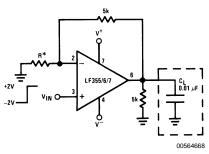
Typical Circuit Connections

Vos Adjustment



- V_{OS} is adjusted with a 25k potentiometer
- The potentiometer wiper is connected to V⁺
- For potentiometers with temperature coefficient of 100 ppm/°C or less the additional drift with adjust is $\approx 0.5 \mu V/$ °C/mV of adjustment
- Typical overall drift: 5µV/°C ±(0.5µV/°C/mV of adj.)

Driving Capacitive Loads



* LF155/6 R = 5k

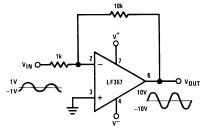
LF357 R = 1.25k

Due to a unique output stage design, these amplifiers have the ability to drive large capacitive loads and still maintain stability. $C_{L(MAX)} \simeq 0.01 \mu F$.

Overshoot ≤ 20%

Settling time $(t_s) \approx 5 \mu s$

LF357. A Large Power BW Amplifier

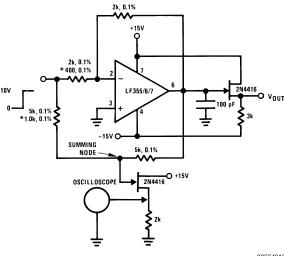


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For distortion \leq 1% and a 20 Vp-p V_{OUT} swing, power bandwidth is: 500kHz.

Typical Applications

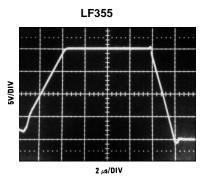
Settling Time Test Circuit



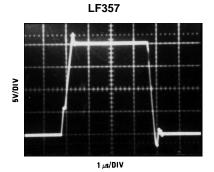
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- Settling time is tested with the LF155/6 connected as unity gain inverter and LF357 connected for $A_V = -5$
- FET used to isolate the probe capacitance
- Output = 10V step
- $A_{V} = -5$ for LF357

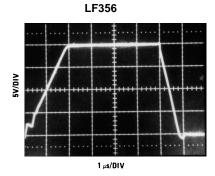
Large Signal Inverter Output, V_{OUT} (from Settling Time Circuit)



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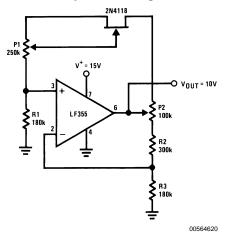


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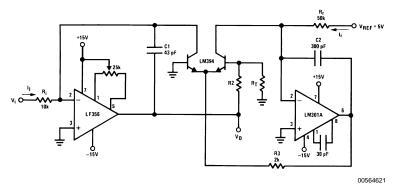
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Low Drift Adjustable Voltage Reference



- $\Delta V_{OUT}/\Delta T = \pm 0.002\%$ °C
- · All resistors and potentiometers should be wire-wound
- · P1: drift adjust
- P2: V_{OUT} adjust
- · Use LF155 for
 - Low I_B
 - Low drift
 - Low supply current

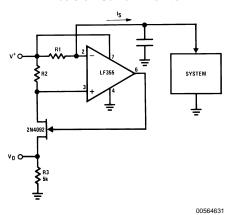
Fast Logarithmic Converter



- Dynamic range: $100\mu\text{A} \le I_i \le 1\text{mA}$ (5 decades), $|V_O| = 1\text{V/decade}$
- Transient response: $3\mu s$ for $\Delta l_i = 1$ decade
- · C1, C2, R2, R3: added dynamic compensation
- \bullet $\,$ $\,$ $\,$ $\,$ $\,$ $\,$ V $_{OS}$ adjust the LF156 to minimize quiescent error
- R_T: Tel Labs type Q81 + 0.3%/°C

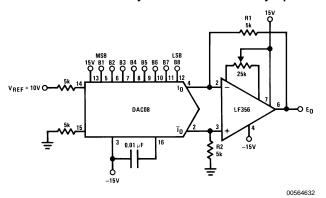
$$|V_{OUT}| = \left[1 + \frac{R2}{R_T}\right] \frac{kT}{q} \text{ in } V_i \left[\frac{R_r}{V_{REF~Ri}}\right] = log~V_i~\frac{1}{R_i I_r}~R2 = 15.7k,~R_T = 1k,~0.3\%/°C~(for~temperature~compensation)$$

Precision Current Monitor



- $V_O = 5 R1/R2 (V/mA of I_S)$
- R1, R2, R3: 0.1% resistors
- Use LF155 for
 - Common-mode range to supply range
 - Low I_B
 - Low V_{OS}
 - Low Supply Current

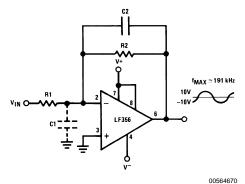
8-Bit D/A Converter with Symmetrical Offset Binary Operation



- R1, R2 should be matched within ±0.05%
- Full-scale response time: 3µs

Eo	В1	B2	В3	В4	B5	B6	В7	В8	Comments
+9.920	1	1	1	1	1	1	1	1	Positive Full-Scale
+0.040	1	0	0	0	0	0	0	0	(+) Zero-Scale
-0.040	0	1	1	1	1	1	1	1	(-) Zero-Scale
-9.920	0	0	0	0	0	0	0	0	Negative Full-Scale

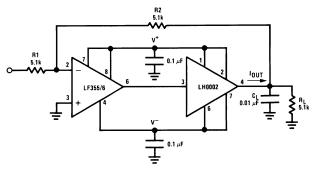
Wide BW Low Noise, Low Drift Amplifier



• Power BW: $f_{MAX} = \frac{S_r}{2\pi V_p} \cong 191 \text{ kHz}$

• Parasitic input capacitance C1 = (3pF for LF155, LF156 and LF357 plus any additional layout capacitance) interacts with feedback elements and creates undesirable high frequency pole. To compensate add C2 such that: R2 C2 = R1 C1.

Boosting the LF156 with a Current Amplifier



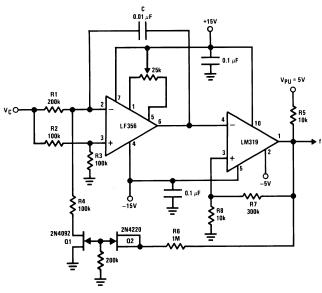
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• $I_{OUT(MAX)} \approx 150 mA$ (will drive $R_L \ge 100 \Omega$)

•
$$\frac{\Delta V_{OUT}}{\Delta T} = \frac{0.15}{10^{-2}} \text{ V/} \mu \text{s (with C}_{L} \text{ shown)}$$

· No additional phase shift added by the current amplifier

3 Decades VCO

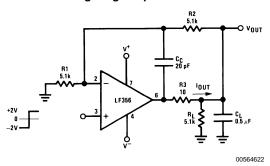


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$$f = \frac{V_{C} (R8 + R7)}{(8 V_{PU} R8 R1) C'} 0 \le V_{C} \le 30V, 10 Hz \le f \le 10 kHz$$

R1, R4 matched. Linearity 0.1% over 2 decades.

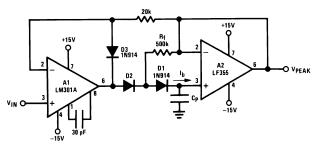
Isolating Large Capacitive Loads



- Overshoot 6%
- t_s 10µs
- When driving large C_L , the V_{OUT} slew rate determined by C_L and $I_{OUT(MAX)}$:

$$\frac{\Delta V_{\rm OUT}}{\Delta T} \,=\, \frac{I_{\rm OUT}}{C_{\rm L}} \,\cong\,\, \frac{0.02}{0.5} \, {\rm V}/\mu {\rm s} \,=\, 0.04 \, {\rm V}/\mu {\rm s} \,\, ({\rm with} \,\, C_{\rm L} \,\, {\rm shown})$$

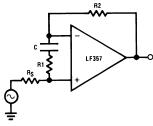
Low Drift Peak Detector



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- By adding D1 and R_f, V_{D1}=0 during hold mode. Leakage of D2 provided by feedback path through R_f.
- Leakage of circuit is essentially I_b (LF155, LF156) plus capacitor leakage of Cp.
- Diode D3 clamps V_{OUT} (A1) to $V_{IN}-V_{D3}$ to improve speed and to limit reverse bias of D2.
- Maximum input frequency should be << $1/2\pi R_f C_{D2}$ where C_{D2} is the shunt capacitance of D2.

Non-Inverting Unity Gain Operation for LF157



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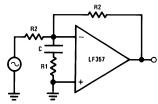
$$R1C \ge \frac{1}{(2\pi) (5 \text{ MHz})}$$

$$R1 = \frac{R2 + R_S}{4}$$

$$A_{V(DC)} = 1$$

$$f_{-3 \text{ dB}} \approx 5 \text{ MHz}$$

Inverting Unity Gain for LF157



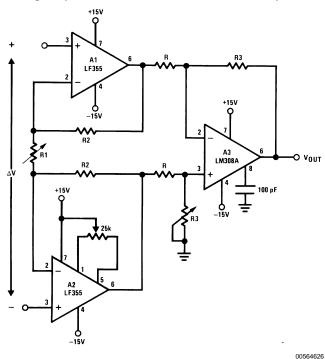
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$$R1C \ge \frac{1}{(2\pi) (5 \text{ MHz})}$$

$$R1 = \frac{R2}{4}$$

$$f_{-3 dB} \approx 5 MHz$$

High Impedance, Low Drift Instrumentation Amplifier



$$\bullet$$
 V_{OUT} = $\frac{R3}{R} \left[\frac{2R2}{R1} + 1 \right] \Delta V$, V⁻ + 2V \leq V_{IN} common-mode \leq V⁺

- System V_{OS} adjusted via A2 V_{OS} adjust
- Trim R3 to boost up CMRR to 120 dB. Instrumentation amplifier resistor array recommended for best accuracy and lowest drift

Fast Sample and Hold The state of the state

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- · Both amplifiers (A1, A2) have feedback loops individually closed with stable responses (overshoot negligible)
- Acquisition time T_A, estimated by:

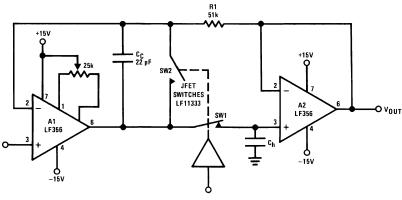
$$T_A \cong \left[\frac{2R_{ON}, V_{IN}, C_h}{S_r}\right] 1/2 \text{ provided that:}$$

$$V_{IN}$$
 < $2\pi S_r R_{ON} C_h$ and T_A > $\frac{V_{IN} C_h}{I_{OUT(MAX)}}$, R_{ON} is of SW1

If inequality not satisfied:
$$T_A \simeq \frac{V_{IN}C_h}{20 \text{ mA}}$$

- LF156 develops full S_r output capability for V_{IN} ≥ 1V
- Addition of SW2 improves accuracy by putting the voltage drop across SW1 inside the feedback loop
- Overall accuracy of system determined by the accuracy of both amplifiers, A1 and A2

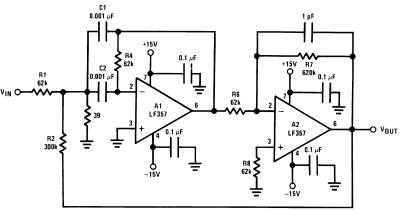
High Accuracy Sample and Hold



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- By closing the loop through A2, the V_{OUT} accuracy will be determined uniquely by A1.
 No V_{OS} adjust required for A2.
- T_A can be estimated by same considerations as previously but, because of the added propagation delay in the feedback loop (A2) the overshoot is not negligible.
- Overall system slower than fast sample and hold
- R1, C_C: additional compensation
- Use LF156 for
 - Fast settling time
 - Low Vos

High Q Band Pass Filter



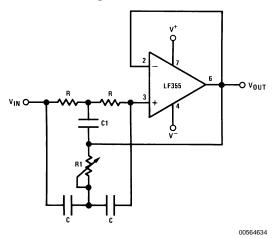
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- By adding positive feedback (R2)
- Q increases to 40
- f_{BP} = 100 kHz

$$\frac{V_{OUT}}{V_{IN}} = 10\sqrt{\overline{Q}}$$

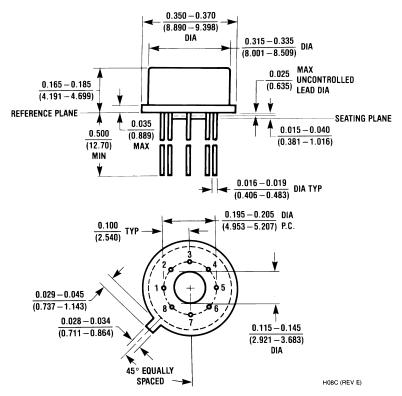
- Clean layout recommended
- Response to a 1Vp-p tone burst: 300µs

High Q Notch Filter

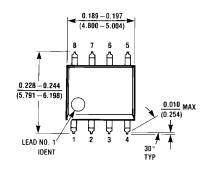


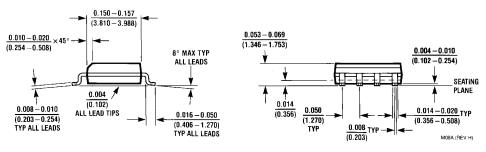
- $2R1 = R = 10M\Omega$ 2C = C1 = 300pF
- · Capacitors should be matched to obtain high Q
- $f_{NOTCH} = 120 \text{ Hz}, \text{ notch} = -55 \text{ dB}, Q > 100$
- Use LF155 for
 - Low I_B
 - Low supply current

Physical Dimensions inches (millimeters) unless otherwise noted



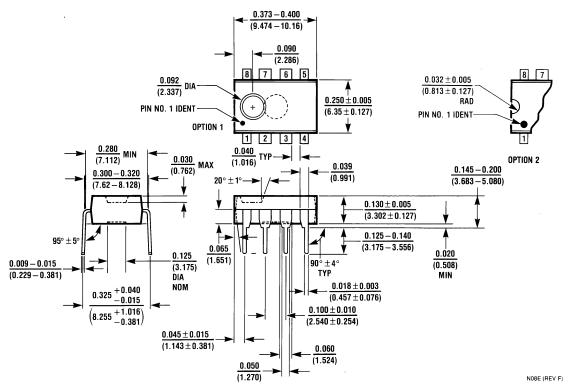
Metal Can Package (H)
Order Number LF155H, LF156H, LF256H, LF257H, LF356BH, LF356H or LF357H
NS Package Number H08C





Small Outline Package (M)
Order Number LF356M or LF356MX
NS Package Number M08A

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



Molded Dual-In-Line Package (N) Order Number LF356N NS Package Number N08E

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- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



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